

SEMICONDUCTOR STRUCTURE AND FABRICATION METHOD THEREFOR

ABSTRACT

A semiconductor structure and a fabrication method therefor, which relate to the technical field of semiconductors, and are used to solve the technical problem of poor performances of semiconductor structures. The fabrication method for a semiconductor structure comprises: providing a substrate (10); forming, on the substrate (10), a plurality of stacked structures (20) arranged at intervals, the stacked structures (20) comprising a first conductive layer (21), an insulating layer (22) and a second conductive layer (23) stacked in sequence, and at least one among the first conductive layer (21) and the second conductive layer (23) being a semi-metal layer; forming a channel layer (30) covering the stacked structures (20), and a dielectric layer (40) covering the channel layer (30); and forming a word line (63) extending along a first direction, the word line (63) comprising a plurality of contact portions (64) and a connection portion (65) that connects adjacent contact portions (64), the contact portions (64) surround and contact the side surface of the dielectric layer (40), and the contact portions (64) are opposite to at least part of the insulating layer (22).

[Fig. 1]